

N-channel 620 V, 2.2 Ω typ., 4.0 A Power MOSFET
in DPAK, I²PAKFP, TO-220 and IPAK packages

Datasheet – preliminary data

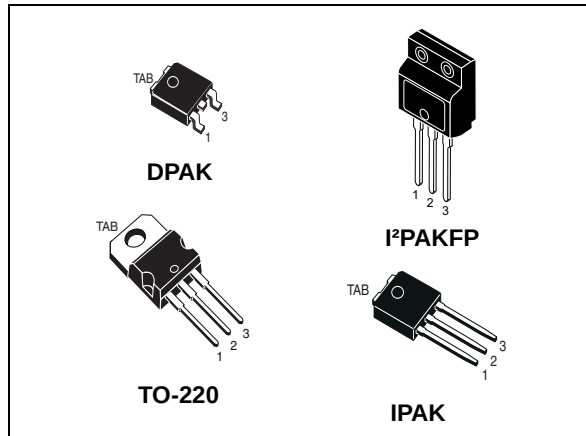
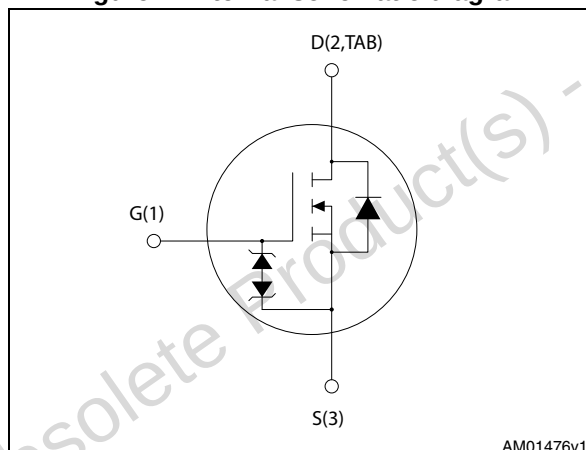


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)} max	I _D	P _{TOT}
STDLED624	620 V	2.5 Ω	4.0 A	45 W
STFILED624				20 W
STPLED624				45 W
STULED624				

- 100% avalanche tested
- Extremely high dv/dt capability
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Applications

- LED lighting applications

Description

These Power MOSFETs boast extremely low on-resistance, superior dynamic performance and high avalanche capability, making them suitable for the buck-boost and flyback topology.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STDLED624	LED624	DPAK	Tape and reel
STFILED624		I ² PAKFP (TO-281)	Tube
STPLED624		TO-220	
STULED624		IPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		DPAK, IPAK	I ² PAKFP	TO-220	
V _{DS}	Drain-source voltage (V _{GS} = 0)	620			V
V _{GS}	Gate- source voltage	± 30			V
I _D	Drain current (continuous) at T _C = 25 °C	4.0	4.0 ⁽¹⁾	4.0	A
I _D	Drain current (continuous) at T _C = 100 °C	2.5	2.5 ⁽¹⁾	2.5	A
I _{DM} ⁽²⁾	Drain current (pulsed)	14	14 ⁽¹⁾	14	A
P _{TOT}	Total dissipation at T _C = 25 °C	45	20	45	W
	Derating factor	0.36	0.16	0.36	W/°C
ESD	Gate-source human body model (C = 100 pF, R = 1.5 kΩ)	2.5			kV
dv/dt ⁽³⁾	Peak diode recovery voltage slope	9			V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)		2500		V
T _{stg}	Storage temperature	-55 to 150			°C
T _j	Max. operating junction temperature	150			°C

1. Limited by package.

2. Pulse width limited by safe operating area.

3. I_{SD} ≤ 2.7 A, di/dt ≤ 200 A/μs, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	TO-220	DPAK	IPAK	I ² PAKFP	Unit
R _{thj-case}	Thermal resistance junction-case max	2.78			6.25	°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max		50			°C/W
R _{thj-amb}	Thermal resistance junction-amb max	62.5			62.5	°C/W

1. When mounted on 1 inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Max. value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	2.7	A
E _{AS}	Single pulse avalanche energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	100	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	620			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 620\text{ V}$ $V_{DS} = 620\text{ V}$, $T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.6	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.4\text{ A}$		2.2	2.5	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	$V_{DS} = 15\text{ V}$, $I_D = 1.4\text{ A}$	-	2.1	-	S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	395 57 7	-	pF pF pF
$C_{OSS\ eq}$ (1)	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }496\text{ V}$	-	33	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	10	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 496\text{ V}$, $I_D = 2.7\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 17)	-	13.5 2.7 7.7	-	nC nC nC

1. $C_{OSS\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{OSS} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off-delay time Fall time	$V_{DD} = 310\text{ V}$, $I_D = 1.7\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 16)	-	9 6.8 22 15.6	-	ns ns ns ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		10.8	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.7 \text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.7 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see Figure 21)	-	190		ns
Q_{rr}	Reverse recovery charge			825		nC
I_{RRM}	Reverse recovery current			9		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.7 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$ (see Figure 21)	-	255		ns
Q_{rr}	Reverse recovery charge			1100		nC
I_{RRM}	Reverse recovery current			10		A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 9. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1 \text{ mA}$ (open drain)	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK, TO-220 and IPAK

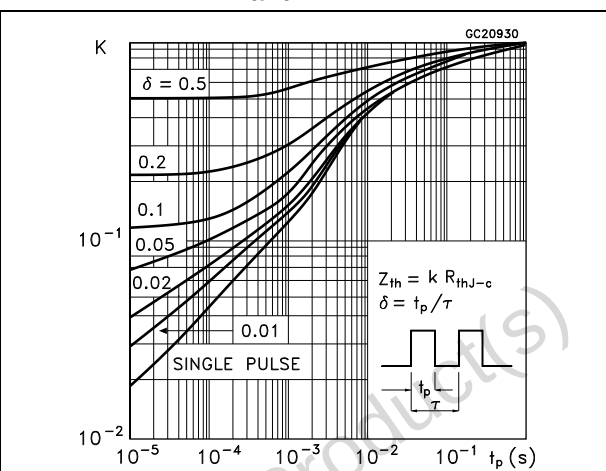
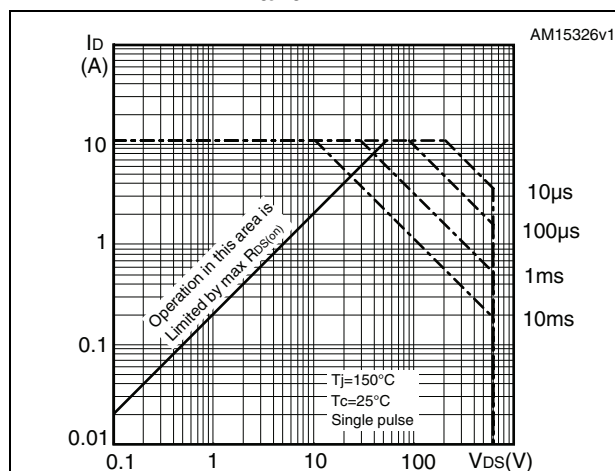


Figure 4. Safe operating area for I²PAKFP

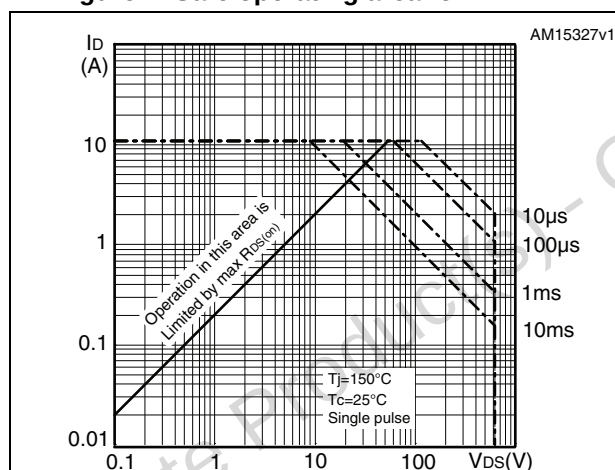


Figure 5. Thermal impedance for I²PAKFP

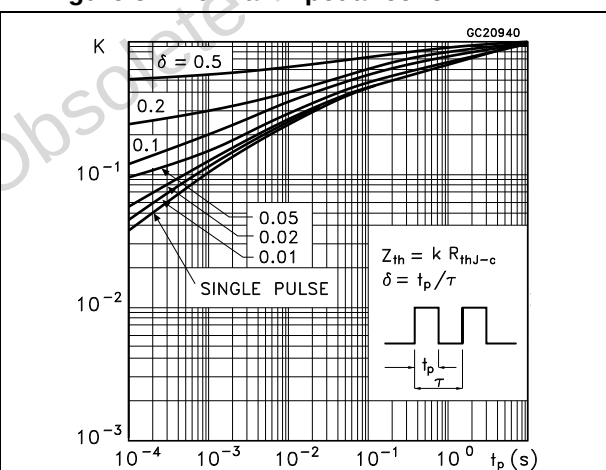


Figure 6. Output characteristics

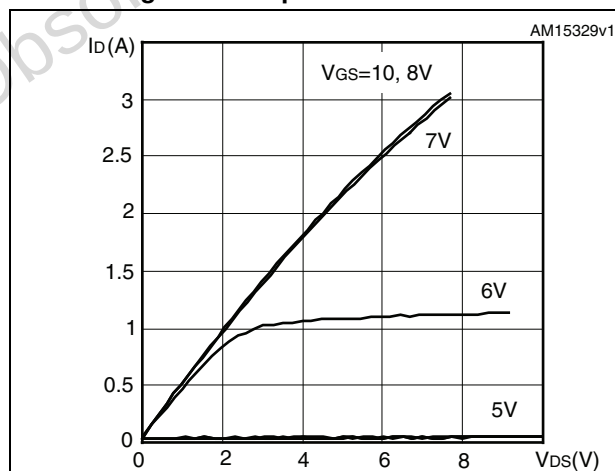


Figure 7. Transfer characteristics

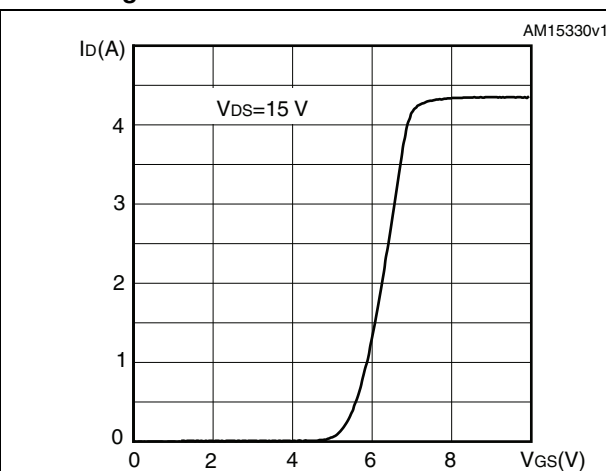


Figure 8. Normalized BV_{DSS} vs temperature

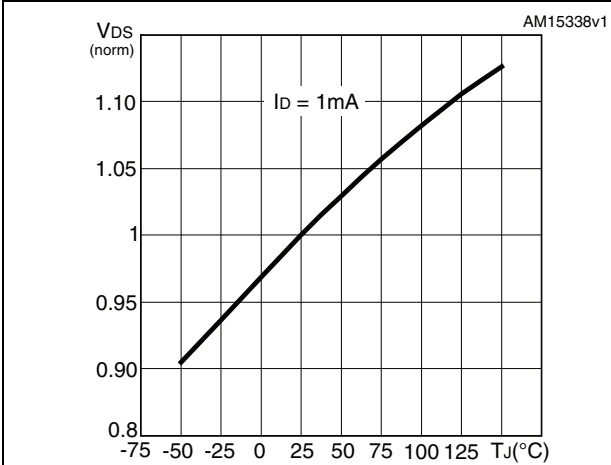


Figure 9. Static drain-source on-resistance

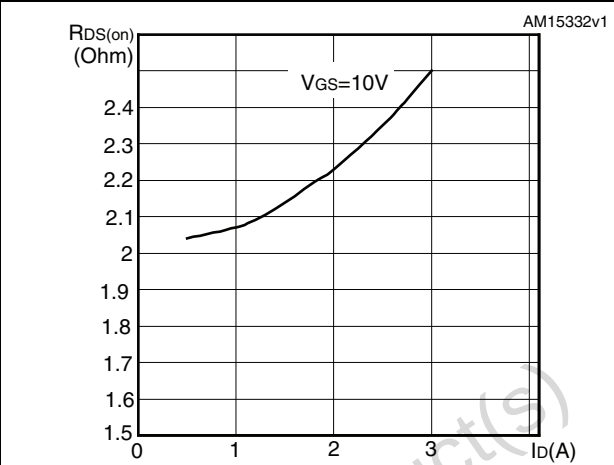


Figure 10. Gate charge vs gate-source voltage

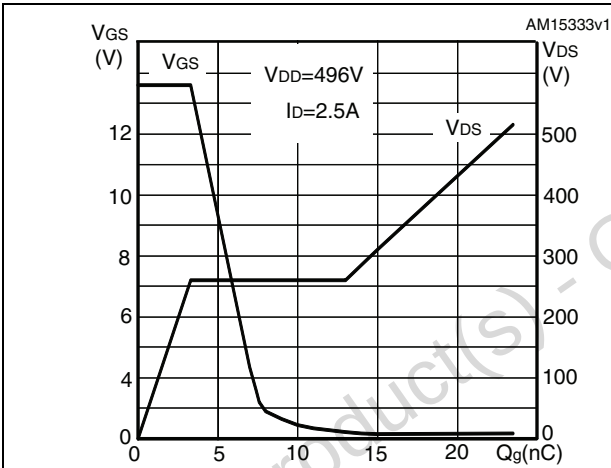


Figure 11. Capacitance variations

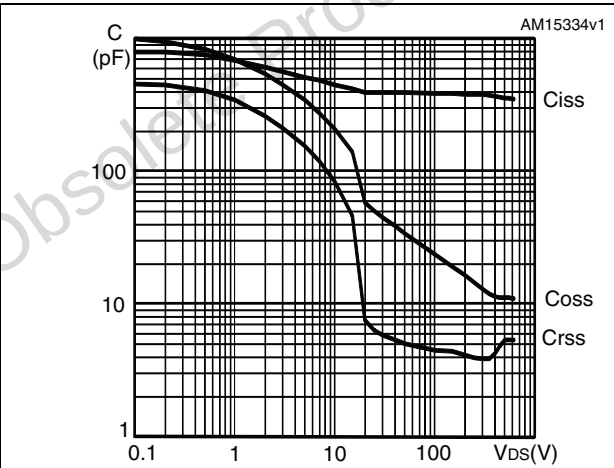


Figure 12. Normalized gate threshold voltage vs temperature

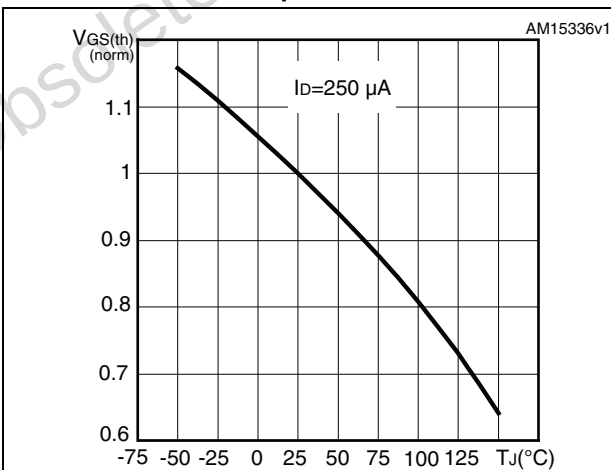


Figure 13. Normalized on-resistance vs temperature

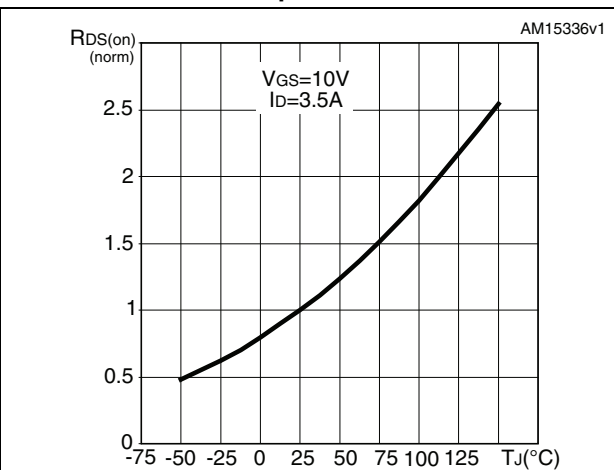


Figure 14. Source-drain diode forward characteristics

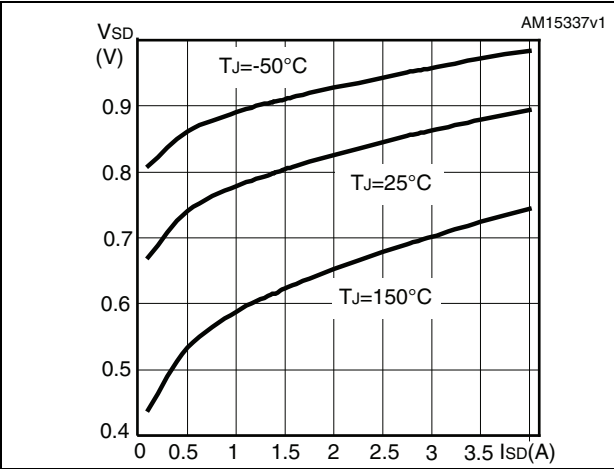
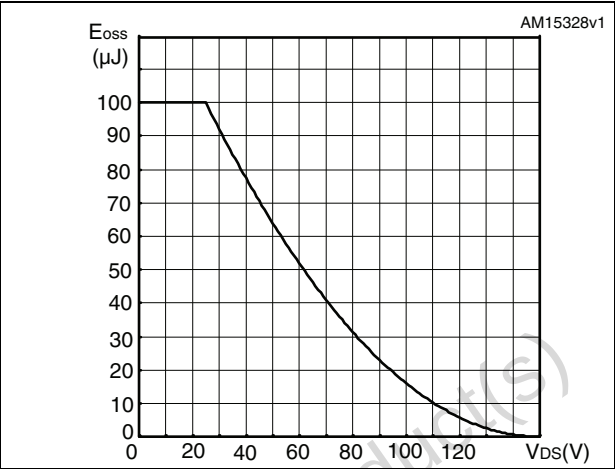


Figure 15. Maximum avalanche energy vs temperature



3 Test circuits

Figure 16. Switching times test circuit for resistive load

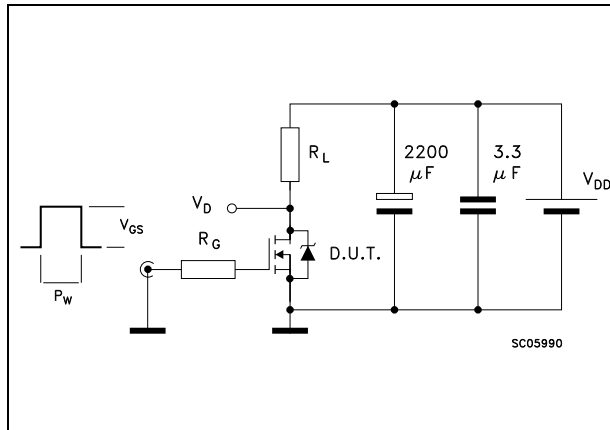


Figure 17. Gate charge test circuit

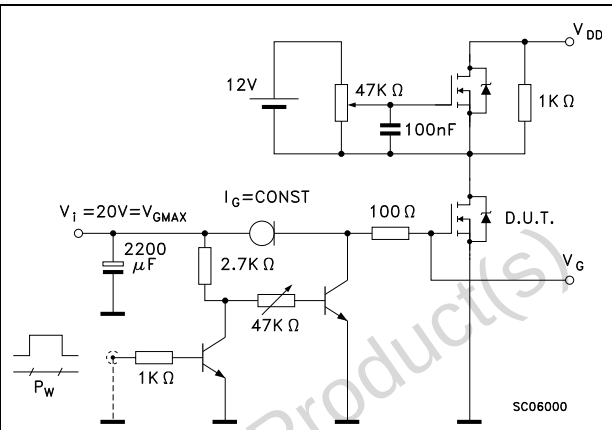


Figure 18. Test circuit for inductive load switching and diode recovery times

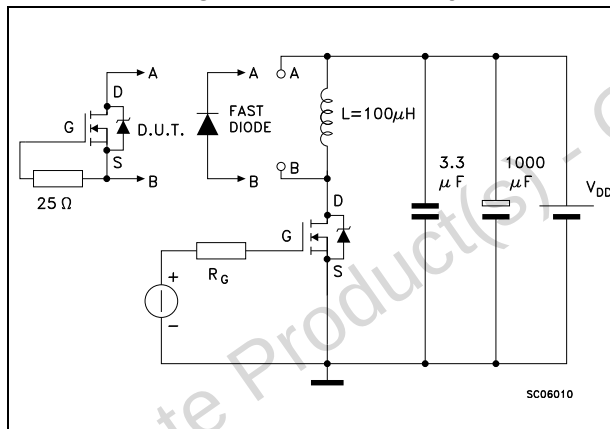


Figure 19. Unclamped Inductive load test circuit

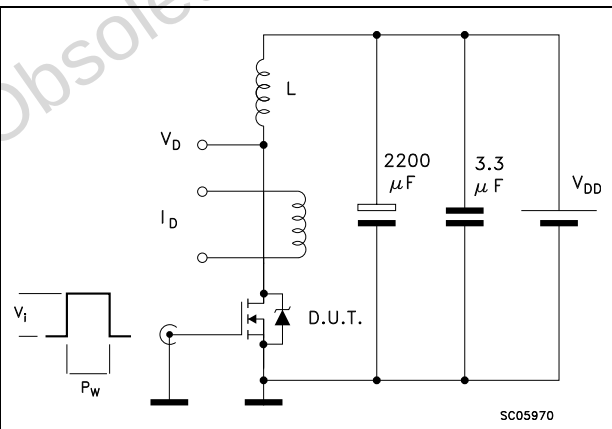


Figure 20. Unclamped inductive waveform

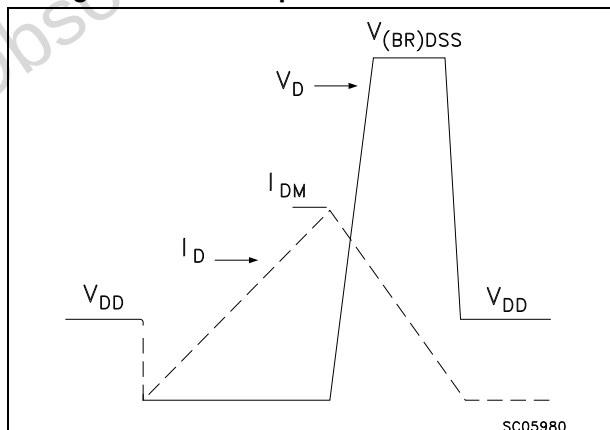
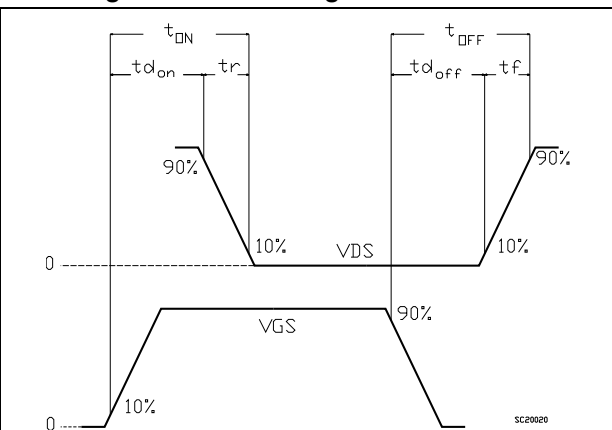


Figure 21. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 22. DPAK (TO-252) drawing

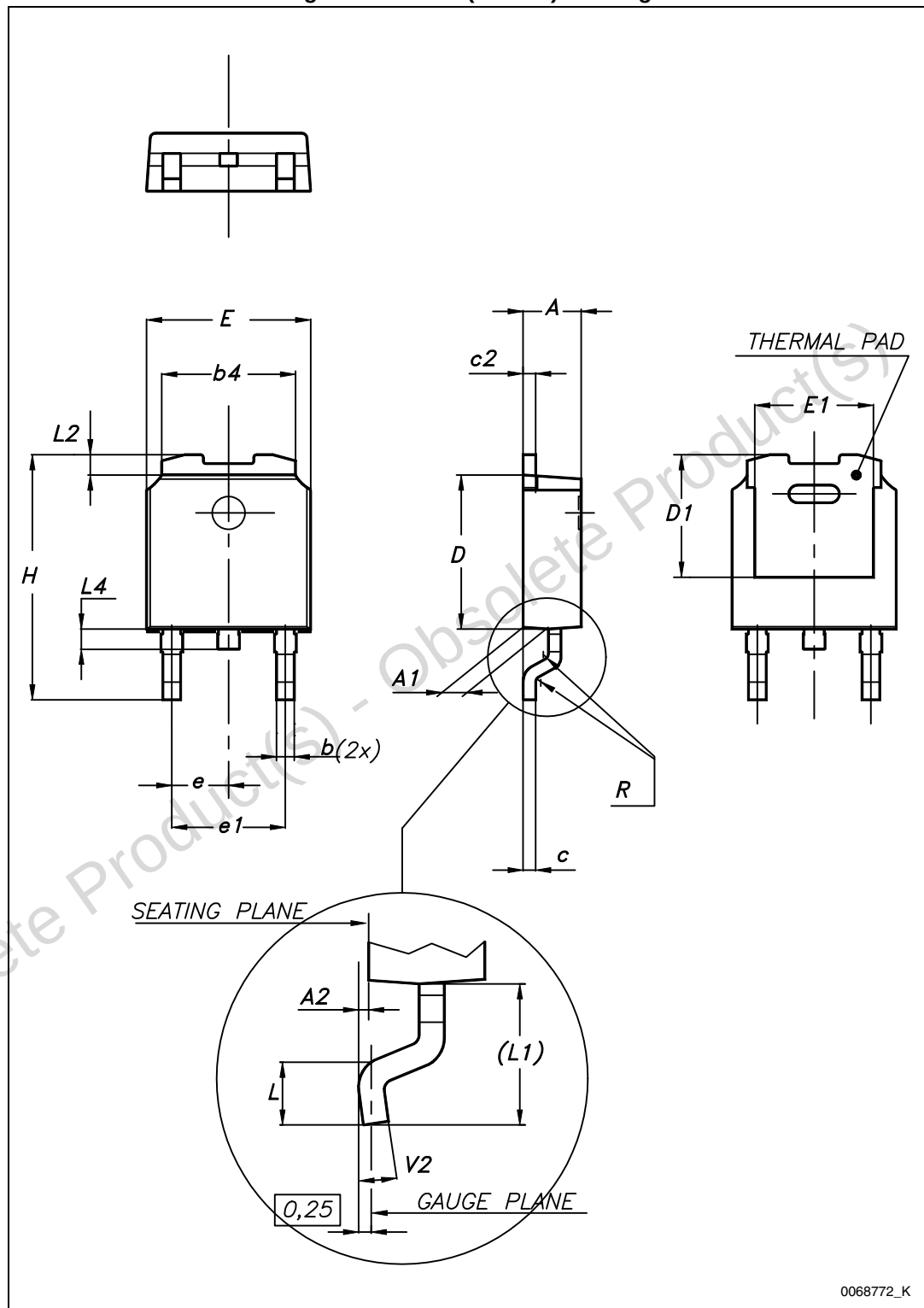
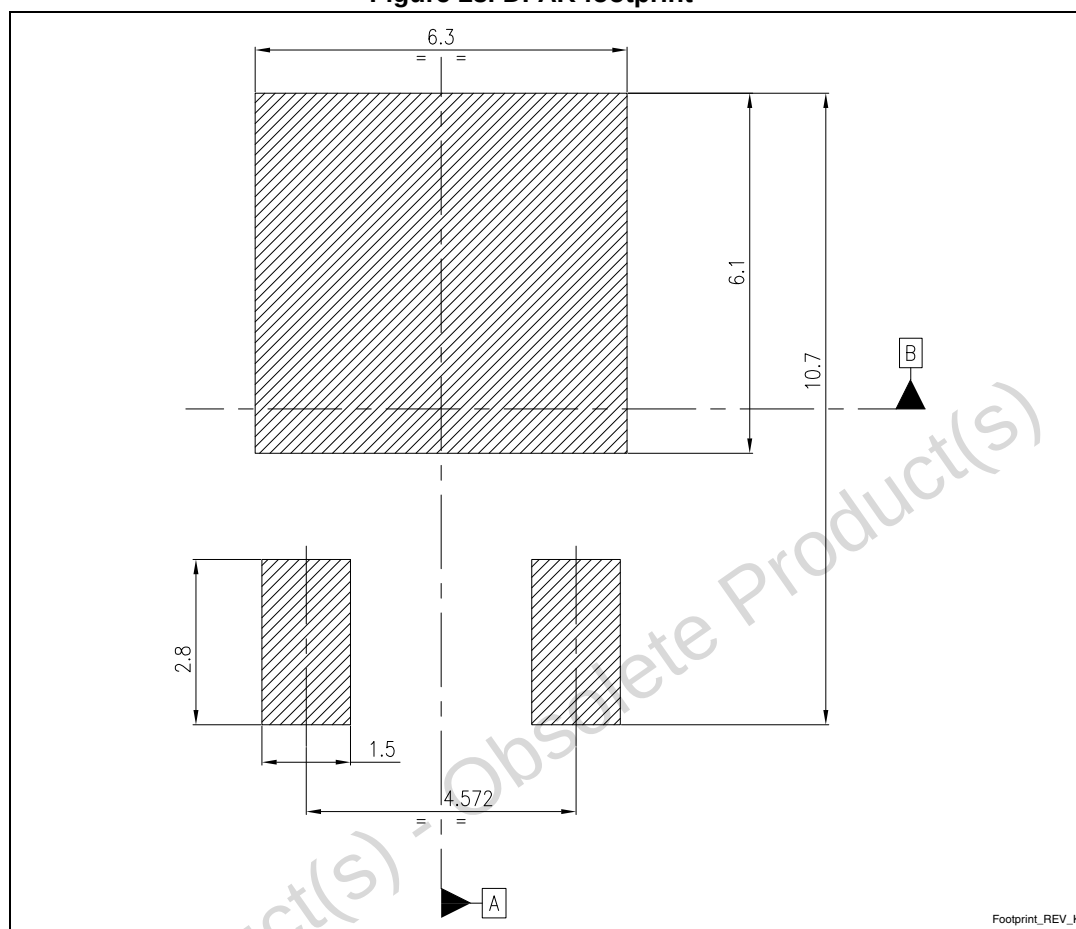


Figure 23. DPAK footprint (a)



a. All dimensions are in millimeters

Table 11. I²PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40	-	4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95		5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

Figure 24. I²PAKFP (TO-281) drawing

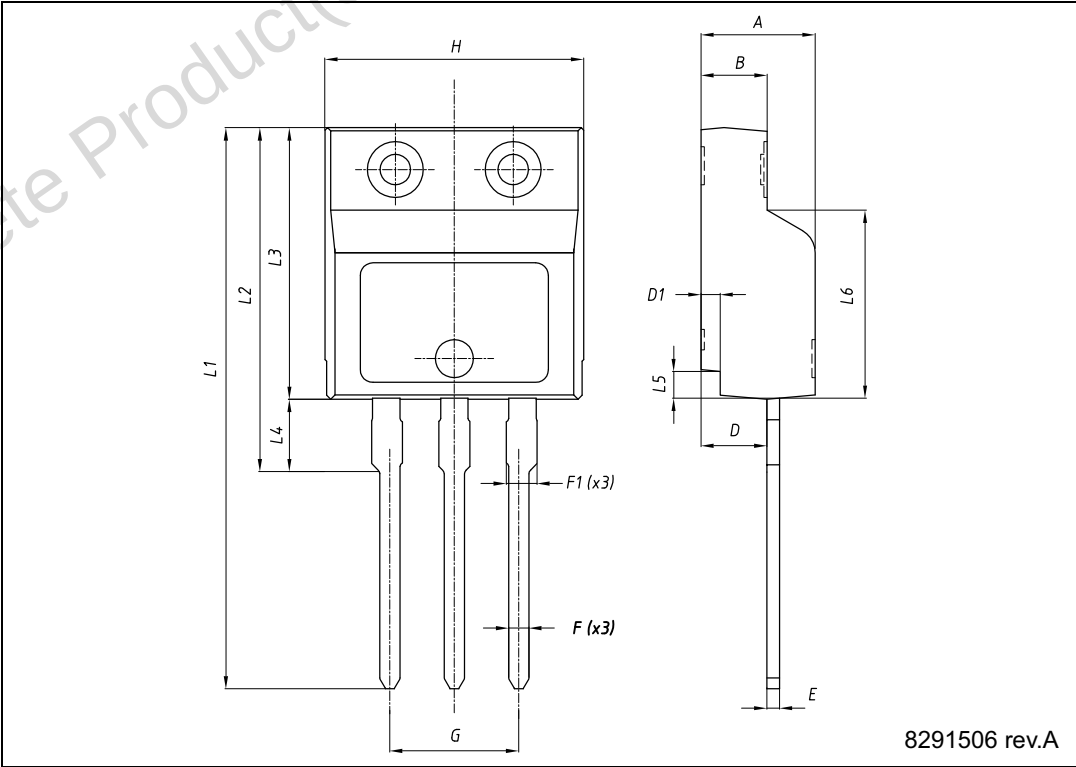


Table 12. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 25. TO-220 type A drawing

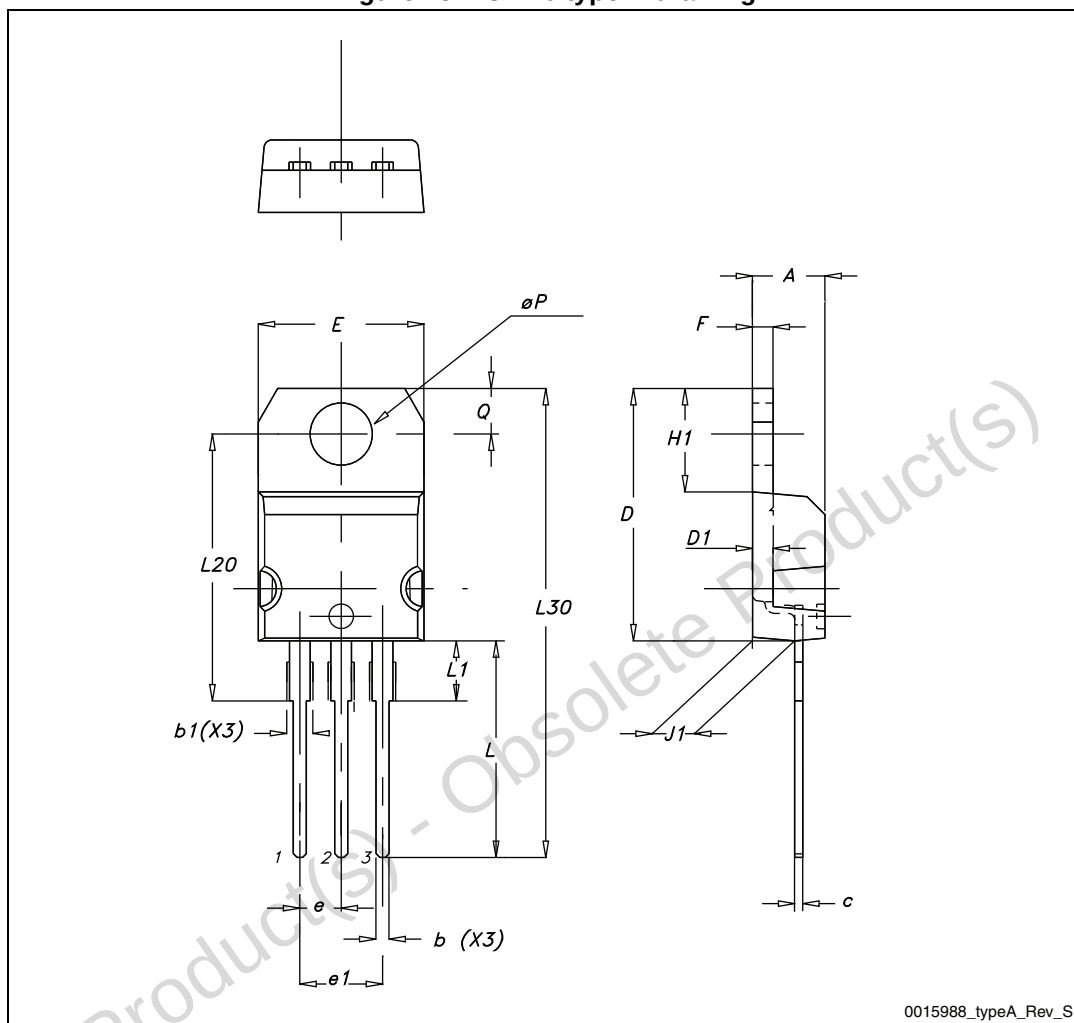
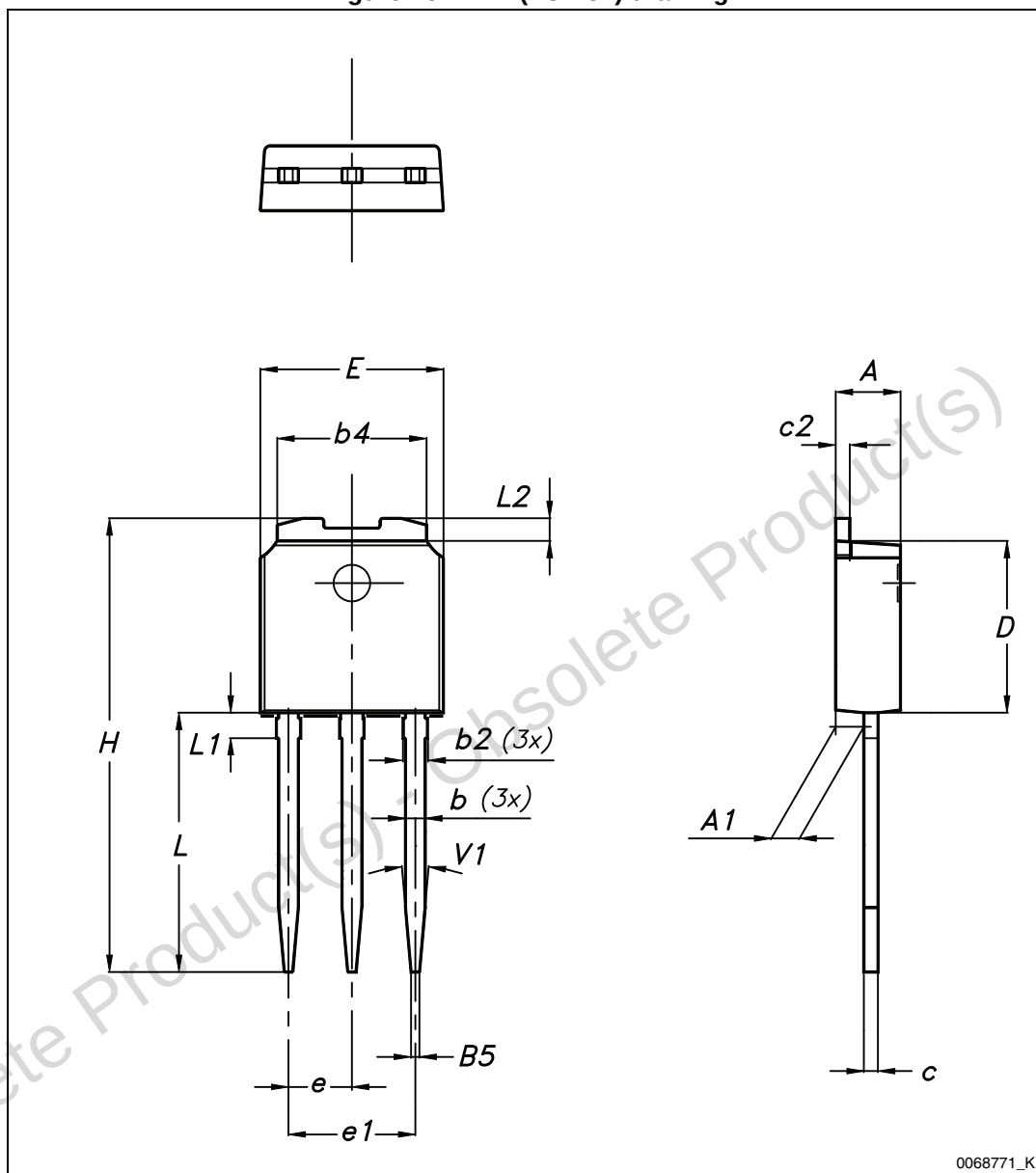


Table 13. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Figure 26. IPAK (TO-251) drawing



5 Packaging mechanical data

Table 14. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 27. Tape for DPAK (TO-252)

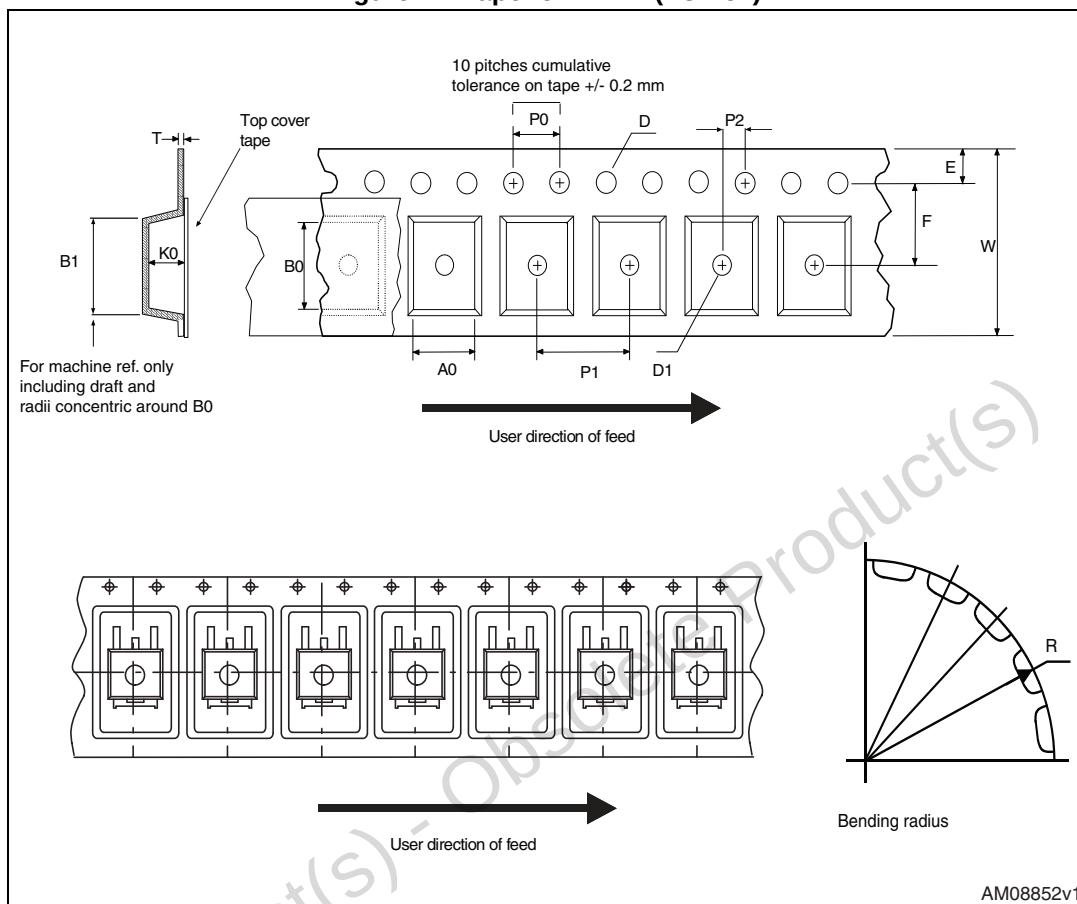
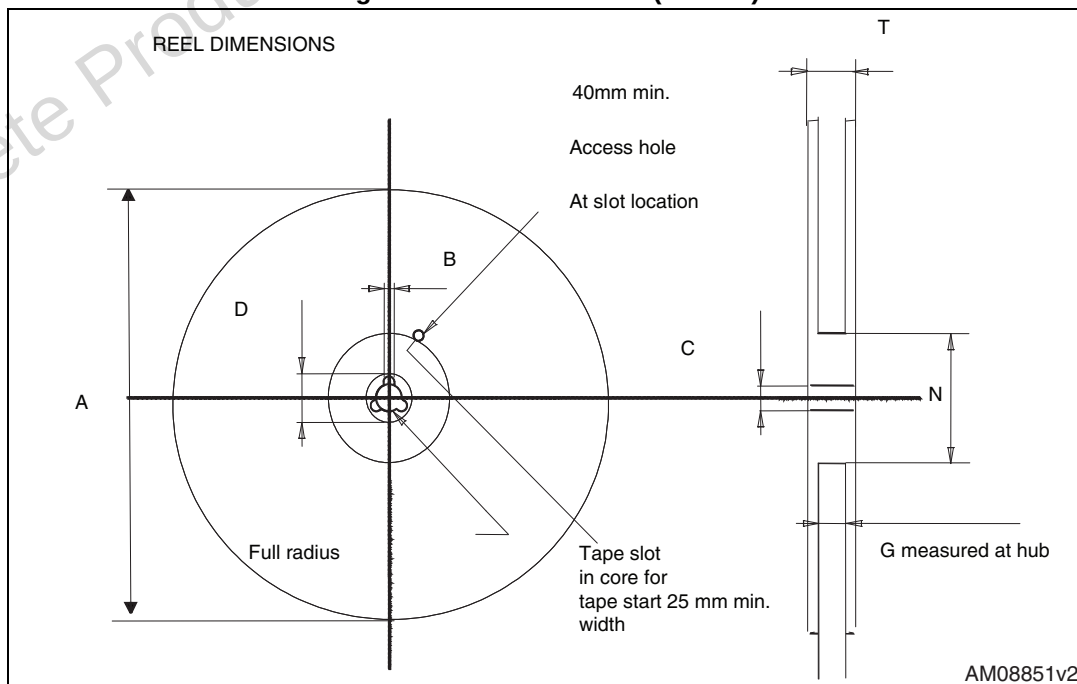


Figure 28. Reel for DPAK (TO-252)



6 Revision history

Table 15. Document revision history

Date	Revision	Changes
21-Mar-2013	1	First release.

Obsolete Product(s) - Obsolete Product(s)

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